

BTA12, BTB12, T12xx

12 A Snubberless™, logic level and standard triacs

Features

- Medium current triac
- Low thermal resistance with clip bonding
- Low thermal resistance insulation ceramic for insulated BTA
- High commutation (4Q) or very high commutation (3Q) capability
- BTA series UL1557 certified (File ref: 81734)
- Packages are RoHS (2002/95/EC) compliant

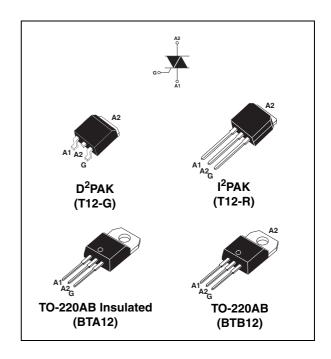
Applications

ON/OFF or phase angle function in applications such as static relays, light dimmers and appliance motors speed controllers.

The snubberless versions (BTA/BTB...W and T12 series) are especially recommended for use on inductive loads, because of their high commutation performances. The BTA series provides an insulated tab (rated at 2500 V RMS).

Description

Available either in through-hole or surface-mount packages, the **BTA12**, **BTB12** and **T12xx** triac series is suitable for general purpose mains power AC switching.



Order code

See Ordering information on page 11

Table 1. Device summary

Symbol	Parameter	T12xx	BTA12 ⁽¹⁾	BTB12
I _{T(RMS)}	RMS on-state current	12	12	12
V _{DRM} /V _{RRM}	Repetitive peak off-state voltage	600/800	600/800	600/800
I _{GT} (Snubberless)	Triggering gate current	10/35/50	5/10/35/50	5/10/35/50
I _{GT} (Standard)	Triggering gate current	-	35/50	35/50

^{1.} Insulated

TM: Snubberless is a trademark of STMicroelectronics

September 2007 Rev 9 1/12

1 Characteristics

Table 2. Absolute maximum ratings

Symbol	Parame		Value	Unit		
I _{T(RMS)}	RMS on-state current (full sine wave)	$ I^{2}PAK / D^{2}PAK / TO-220AB $ $ T_{c} = 105^{\circ} C$		12	А	
- 7	(iuii sirie wave)	TO-220AB Ins.	T _C = 90° C			
1.	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	120	Α	
I _{TSM}	current (full cycle, T _j initial = 25° C)	= 25° C) F = 60 Hz		126	A	
I ² t	I ² t Value for fusing	t _p = 10 ms		78	A ² s	
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$	F = 120 Hz	T _j = 125° C	50	A/μs	
V _{DSM} /V _{RSM}	Non repetitive surge peak off-state voltage $t_p = 10 \text{ ms} \qquad \qquad T_j = 25^{\circ} \text{ C}$		V _{DRM} /V _{RRM} + 100	V		
I _{GM}	Peak gate current $t_p = 20 \mu s$ $T_j = 125^{\circ} C$		4	Α		
$P_{G(AV)}$	Average gate power dissipation	1	W			
T _{stg} T _j	Storage junction temperature range Operating junction temperature range	- 40 to + 150 - 40 to + 125	°C			

Table 3. Electrical characteristics ($T_j = 25^{\circ}C$, unless otherwise specified) Snubberless and logic level (3 quadrants)

Symbol	Test conditions	nditions Quadrant			T12xx		E	BTA12	BTB1	2	Unit
Symbol	rest conditions	Quadrant		T1210	T1235	T1250	TW	sw	CW	BW	Offic
I _{GT} ⁽¹⁾	V _D = 12 V	1 - 11 - 111	MAX.	10	35	50	5	10	35	50	mA
V _{GT}	$R_L = 30 \Omega$	1 - 11 - 111	MAX.				1.3				V
V _{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_j = 125^{\circ} \text{ C}$	1 - 11 - 111	MIN.			(0.2				V
I _H ⁽²⁾	I _T = 100 mA		MAX.	15	35	50	10	15	35	50	mA
1	1 101	1 - 111	MAX.	25	50	70	10	25	50	70	mA
IL	$I_{G} = 1.2 I_{GT}$	II	WAX.	30	60	80	15	30	60	80	ША
dV/dt ⁽²⁾	$V_D = 67 \text{ %V}_{DRM}$ gate open $T_j = 125^{\circ} \text{ C}$		MIN.	40	500	1000	20	40	500	1000	V/µs
	$(dV/dt)c = 0.1 V/\mu s$ $T_j = 125^{\circ} C$			6.5			3.5	6.5			
(dl/dt)c (2)	$(dV/dt)c = 10 V/\mu s$ $T_j = 125^{\circ} C$		MIN.	2.9			1	2.9			A/ms
	Without snubber T _j = 125° C				6.5	12			6.5	12	

^{1.} Minimum I_{GT} is guaranted at 5% of I_{GT} max

^{2.} for both polarities of A2 referenced to A1

Table 4. Electrical characteristics ($T_j = 25$ °C, unless otherwise specified) standard (4 quadrants)

Symbol	Test Conditions	Quadrant		BTA12 / BTB12		Unit
Symbol	rest Conditions	Guaurant		С	В	Onit
I _{GT} ⁽¹⁾	$V_D = 12 \text{ V}$ $R_L = 30 \Omega$	I - II - III IV	MAX.	25 50	50 100	mA
V _{GT}	V _{GT}		MAX.	1.3		V
V_{GD}	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_j = 125^{\circ} \text{ C}$ ALL		MIN.	0.2		٧
I _H ⁽²⁾	I _T = 500 mA		MAX.	25	50	mA
1	$I_G = 1.2 I_{GT}$	I - III - IV	MAX.	40	50	mA
ال	IG = 1.2 IGT	II	IVIAA.	80	100	IIIA
dV/dt (2)	$V_D = 67\% V_{DRM}$ gate open $T_j = 125^{\circ} C$			200	400	V/µs
(dV/dt)c (2)	(dl/dt)c = 5.3 A/ms $T_j = 125^{\circ} C$		MIN.	5	10	V/µs

^{1.} Minimum $I_{\mbox{\scriptsize GT}}$ is guaranted at 5% of $I_{\mbox{\scriptsize GT}}$ max.

Table 5. Static characteristics

Symbol	Test cor	Value	Unit		
V _T ⁽¹⁾	$I_{TM} = 17 \text{ A}$ $t_p = 380 \mu\text{s}$	T _j = 25° C	MAX.	1.55	V
V _{t0} ⁽¹⁾	Threshold voltage	T _j = 125° C	MAX.	0.85	V
R _d ⁽¹⁾	Dynamic resistance	$T_{j} = 125^{\circ} \text{ C}$ MAX.		35	mΩ
I _{DRM}	V - V	T _j = 25° C	MAX.	5	μΑ
I _{RRM}	$V_{DRM} = V_{RRM}$	T _j = 125° C	IVIAA.	1	mA

^{1.} for both polarities of A2 referenced to A1

Table 6. Thermal resistance

Symbol	Parameter			Value	Unit
В	lunction to cope (AC)		I ² PAK / D ² PAK / TO-220AB	1.4	°C/W
R _{th(j-c)} Junction to case (AC)			TO-220AB insulated	2.3	C/VV
	Junction to ambient	$S^{(1)} = 1 \text{ cm}^2$	D ² PAK	45	
R _{th(j-a)}			TO-220AB / I ² PAK TO-220AB insulated	60	°C/W

1. Copper surface under tab.

^{2.} for both polarities of A2 referenced to A1.

Figure 1. Maximum power dissipation versus Figure 2. RMS on-state current versus case RMS on-state current (full cycle) temperature (full cycle)

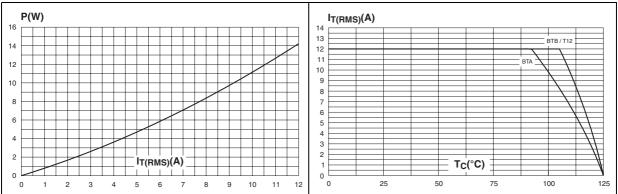


Figure 3. RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35µm) (full cycle)

Figure 4. Relative variation of thermal impedance versus pulse duration

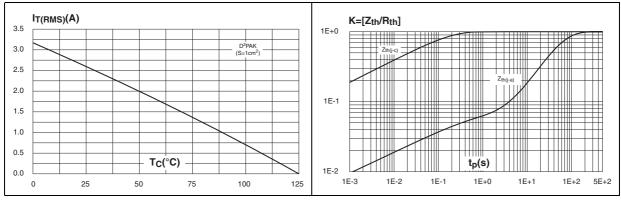


Figure 5. On-state characteristics (maximum Figure 6. Surge peak on-state current versus values)

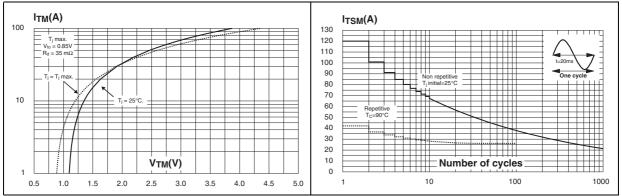
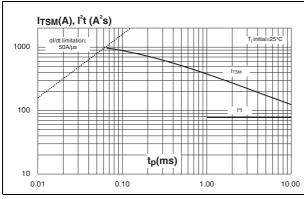


Figure 7. Non-repetitive surge peak on-state Figure 8. current for a sinusoidal pulse with width $t_p < 10 \text{ ms}$ and corresponding value of I^2t

igure 8. Figure 8: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)



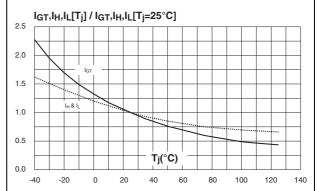
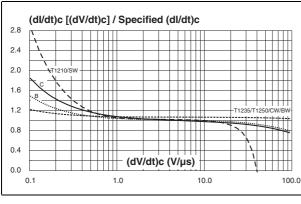


Figure 9. Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values) (BW/CW/T1210/T1235)

Figure 10. Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values) (TW)



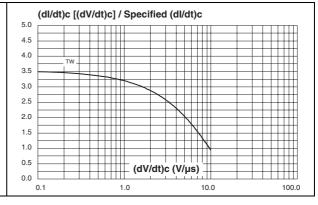
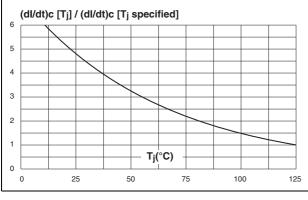
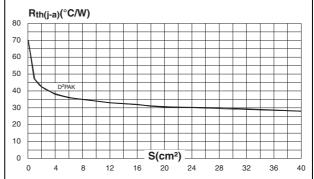


Figure 11. Relative variation of critical rate of Figure 12. decrease of main current versus junction temperature

D²PAK thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: 35 μm)





2 Ordering information scheme

Figure 13. BTA12 and BTB12 series

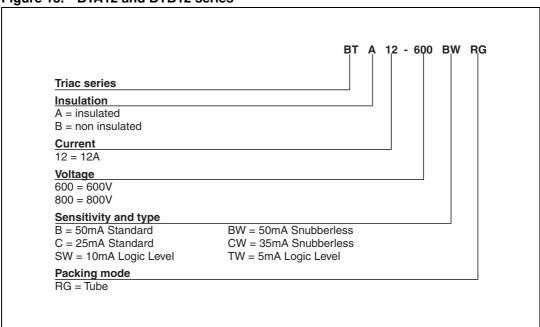


Figure 14. T12xx series

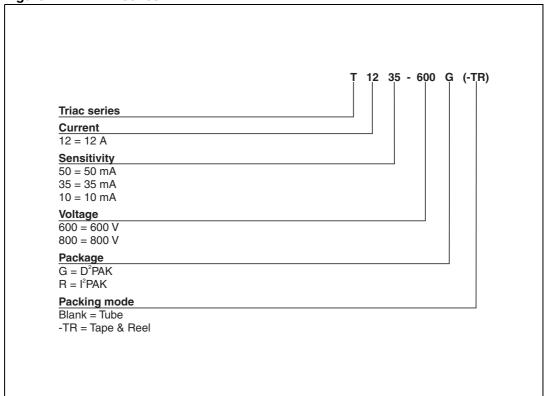


Table 7. Product selector

Order code ⁽¹⁾	Voltage (xxx)		Consitivity	Tyme	Pookogo	
Order code.	600 V	800 V	Sensitivity	Туре	Package	
BTA/BTB12-xxxBRG	Х	Х	50 mA	Standard	TO-220AB	
BTA/BTB12-xxxBWRG	Х	Х	50 mA	Snubberless	TO-220AB	
BTA/BTB12-xxxCRG	Х	Х	25 mA	Standard	TO-220AB	
BTA/BTB12-xxxCWRG	Х	Х	35 mA	Snubberless	TO-220AB	
BTA/BTB12-xxxSWRG	Х	Х	10 mA	Logic Level	TO-220AB	
BTA/BTB12-xxxTWRG	Х	Х	5 mA	Logic Level	TO-220AB	
T1210-800G	-	Х	10 mA	Logic Level	D ² PAK	
T1235-xxxG	Х	Х	35 mA	Snubberless	D ² PAK	
T1235-xxxR	Х	Х	35 mA	Snubberless	I ² PAK	
T1250-600G	Х	-	50 mA	Snubberless	D ² PAK	

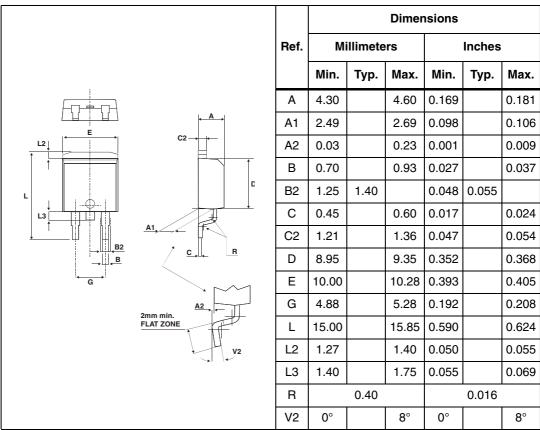
^{1.} BTB: non insulated TO-220AB package

3 Packaging information

Epoxy meets UL94, V0

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Table 8. D²PAK dimensions



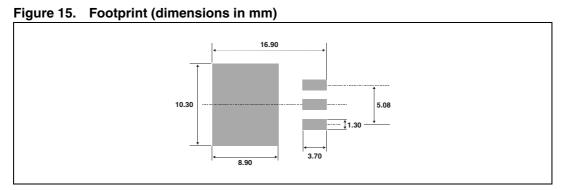
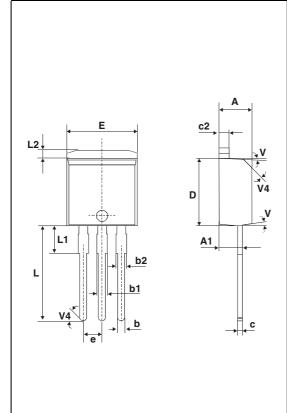


Table 9. I²PAK dimensions



	Dimensions						
Ref.	Mi	Millimete			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	4.30		4.60	0.169		0.181	
A1	2.49		2.69	0.098		0.106	
b	0.70		0.93	0.028		0.037	
b1	1.20		1.38	0.047		0.054	
b2	1.25	1.40		0.049	0.055		
С	0.45		0.60	0.018		0.024	
c2	1.21		1.36	0.048		0.054	
D	8.95		9.35	0.352		0.368	
е	2.44		2.64	0.096		0.104	
Е	10.00		10.28	0.394		0.405	
L	13.10		13.60	0.516		0.535	
L1		3.75			0.148		
L2	1.27		1.40	0.050		0.055	
٧		5°			5°		
V4		45°			45°		

Dimensions Ref. Millimeters **Inches** Min. Тур. Max. Min. Тур. Max. 15.20 15.90 0.598 0.625 Α a1 3.75 0.147 В a2 13.00 14.00 0.511 0.551 В 10.00 10.40 0.393 0.409 ÎL b1 0.61 0.88 0.024 0.034 1.23 0.051 b2 1.32 0.048 14 С 4.40 4.60 0.173 0.181 13 с1 0.49 0.70 0.019 0.027 c2 c2 2.40 2.72 0.094 0.107 2.40 0.094 0.106 2.70 е F 6.20 6.60 0.244 0.259 ØΙ 3.75 3.85 0.147 0.151 0.661 14 15.80 16.40 16.80 0.622 0.646 L 2.65 2.95 0.104 0.116 12 1.14 0.044 0.066 1.70 13 1.14 1.70 0.044 0.066 Μ 0.102 2.60

Table 10. TO-220AB dimensions (insulated and non-insulated)

4 Ordering information

Table 11. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
BTA/BTB12-xxxyzRG	BTA/BTB12-xxxyz	TO-220AB	2.3 g	50	Tube
T1210-xxxG-TR	T1210-xxxG	D ² PAK	1.5 g	1000	Tape and reel
T1235-xxxG	T1235xxxG	D ² PAK	150	50	Tube
T1235-xxxG-TR	T1235xxxG	DIFAN	1.5 g	1000	Tape and reel
T1235-xxxR	T1235-xxxR	I ² PAK	1.5 g	50	Tube
T1250-xxxG-TR	T1250xxxG	D ² PAK	1.5 g	1000	Tape and reel

Note: xxx = voltage, y = sensitivity, z = type

5 Revision history

Table 12. Revision history

Date	Date Revision Changes		
Sep-2002	6A	Last update.	
25-Mar-2005	7	 I²PAK package added. TO-220AB delivery mode changed from bulk to tube. 	
27-May-2005	8	T1210 added	
28-Sep-2007	9	Reformatted to current standards. T1250 added	

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